

L Number	Hits	Search Text	DB	Time stamp
4	1	("5990496").PN.	USPAT; US-PGPUB	2004/08/24 13:12
5	37	nitride near3 semiconductor near3 laser and (ingan same (current near3 block\$3))	USPAT; US-PGPUB	2004/08/24 13:15
6	3	nitride near3 semiconductor near3 laser and (ingan near3 (current near3 block\$3)) and ridge	USPAT; US-PGPUB	2004/08/24 14:33
7	1	nitride near3 semiconductor near3 laser and (current near3 block\$3 near3 (multilayer or multi-layer or multi near layer)) and ridge	USPAT; US-PGPUB	2004/08/24 14:35
8	1	nitride near3 semiconductor near3 laser and (current near3 block\$3 near3 (multilayer or multi-layer or multi near layer)) and ridge	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/24 14:36
9	10	nitride and (current near3 block\$3 near3 (multilayer or multi-layer or multi near layer)) and ridge	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/24 14:36
10	12	nitride and (current near3 block\$3 near3 (multilayer\$1 or multi-layer\$1 or (multi near layer\$1) or (multiple near3 layer\$1))) and ridge	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/24 14:41
11	20	nitride and (current near3 block\$3 near3 (multilayer\$1 or multi-layer\$1 or (multi near layer\$1) or (multiple near3 layer\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/24 16:23
12	1	("6031858").PN.	USPAT; US-PGPUB	2004/08/24 15:45
13	11	cap near3 contact near3 layer\$1 and nitride near3 semiconductor near3 laser	USPAT; US-PGPUB	2004/08/24 15:46
14	14	nitride near3 based near3 laser and (current near3 block\$3 same (multilayer\$1 or multi-layer\$1 or (multi near layer\$1) or (multiple near3 layer\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/24 16:24
-	109	nitride near3 semiconductor near3 laser and (current near3 (block\$3 or confin\$9)) and ridge	USPAT; US-PGPUB	2004/08/23 15:07
-	13	((nitride near3 base\$1) or (nitride-base\$1)) and ((buried near3 ridge) or (buried-ridge)) and (current near3 (block\$3 or confin\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/23 16:30
-	3	((mocvd or (chemical near3 vapor near3 deposition)) same (transverse near3 growth))	USPAT; US-PGPUB	2004/08/23 17:22
-	4	((mocvd or (chemical near3 vapor near3 deposition)) same (transverse near3 growth))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/23 17:23
-	1	((((mocvd or (chemical near3 vapor near3 deposition)) same (transverse near3 growth))) not (((mocvd or (chemical near3 vapor near3 deposition)) same (transverse near3 growth))))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/23 17:22
-	68	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/23 17:23
-	5	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth near3 technique))	USPAT; US-PGPUB	2004/08/23 17:31
-	0	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth near3 technique))	EPO; JPO; DERWENT	2004/08/23 17:29
-	66	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth))	USPAT; US-PGPUB	2004/08/23 17:30
-	5	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth near3 technique))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/23 17:32
-	9	((mocvd or (chemical near3 vapor near3 deposition)) and (transverse near3 growth near3 (technique or process or procedure or method)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/08/23 17:33